NEW PRODUCT

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Q1 N-CHANNEL	Q2 P-CHANNEL	Units
Drain-Source Voltage			V_{DSS}	12	-12	V
Gate-Source Voltage			V_{GSS}	±8	±8	V
Continuous Drain Current (Note 5) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	5.6 4.4	-3.8 -3.0	A
	t < 5s	T_A = +25°C T_A = +70°C	I_D	7.2 5.8	-5.0 -4.0	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	1	-1	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	20	-15	A
Avalanche Current (L = 0.1mH)			I_{AS}	15	-12	A
Avalanche Energy (L = 0.1mH)			E_{AS}	12	8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	Steady State	P_D	1.4	W
	t < 5s		2.2	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	91	°C/W
	t < 5s		55	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	20	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Note: 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

NEW PRODUCT

Electrical Characteristics Q1 N-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	12	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1.0	µA	V_{DS} = 12V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.4	—	1	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	17	29	mΩ	V_{GS} = 4.5V, I_D = 5A
		—	20	34		V_{GS} = 2.5V, I_D = 4.6A
		—	24	44		V_{GS} = 1.8V, I_D = 4.1A
		—	30	65		V_{GS} = 1.5V, I_D = 2A
Diode Forward Voltage	V_{SD}	—	0.6	1.2	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	914	—	pF	V_{DS} = 6V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	132	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	119	—	pF	
Gate Resistance	R_g	—	1.26	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	10.5	—	nC	V_{DS} = 6V, I_D = 6.5A
Total Gate Charge (V_{GS} = 8V)		—	19.6	—	nC	
Gate-Source Charge	Q_{gs}	—	1.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.6	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.0	—	ns	V_{DD} = 6V, V_{GS} = 4.5V, R_L = 1.2Ω, R_G = 1Ω
Turn-On Rise Time	t_R	—	10.5	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	16.6	—	ns	
Turn-Off Fall Time	t_F	—	4.1	—	ns	

Electrical Characteristics Q2 P-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-12	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1.0	µA	V_{DS} = -12V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.4	—	-1	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	37	61	mΩ	V_{GS} = -4.5V, I_D = -3.6A
		—	47	81		V_{GS} = -2.5V, I_D = -3.2A
		—	63	115		V_{GS} = -1.8V, I_D = -1A
		—	90	210		V_{GS} = -1.5V, I_D = -1A
Diode Forward Voltage	V_{SD}	—	-0.65	-1.2	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	915	—	pF	V_{DS} = -6V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	225	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	183	—	pF	
Gate Resistance	R_g	—	56.9	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	10.7	—	nC	V_{DS} = -6V, I_D = -4.3A
Total Gate Charge (V_{GS} = -8V)		—	17.9	—	nC	
Gate-Source Charge	Q_{gs}	—	1.7	—	nC	
Gate-Drain Charge	Q_{gd}	—	3.0	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.7	—	ns	V_{DD} = -6V, V_{GS} = -4.5V, R_L = 1.6Ω, R_G = 1Ω
Turn-On Rise Time	t_R	—	11.5	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	27.8	—	ns	
Turn-Off Fall Time	t_F	—	26.4	—	ns	

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

NEW PRODUCT

Typical Characteristics - N-CHANNEL

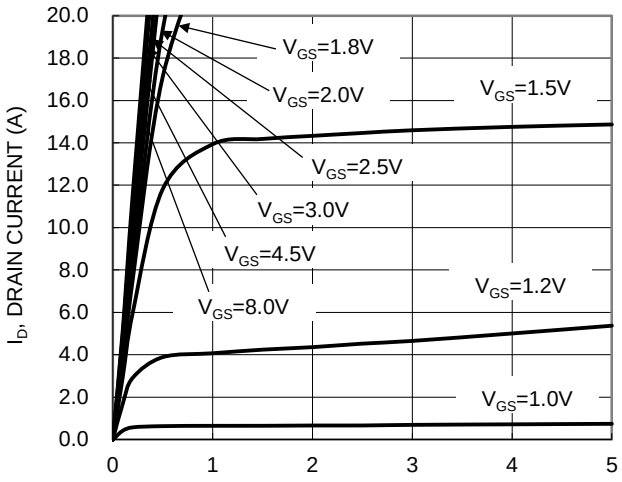

Figure 1. Typical Output Characteristic

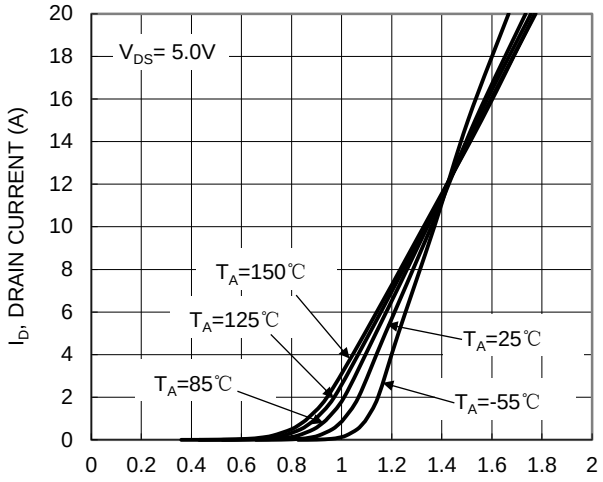

Figure 2. Typical Transfer Characteristic

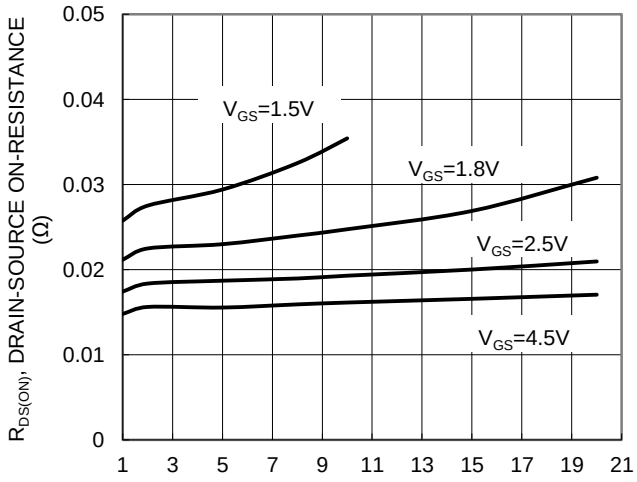

Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

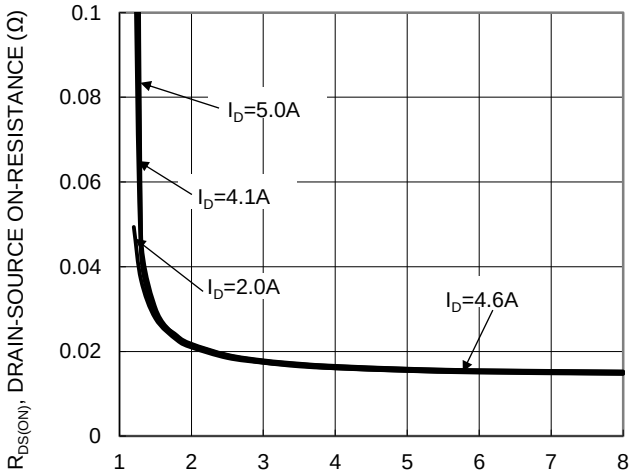

Figure 4. Typical Transfer Characteristic

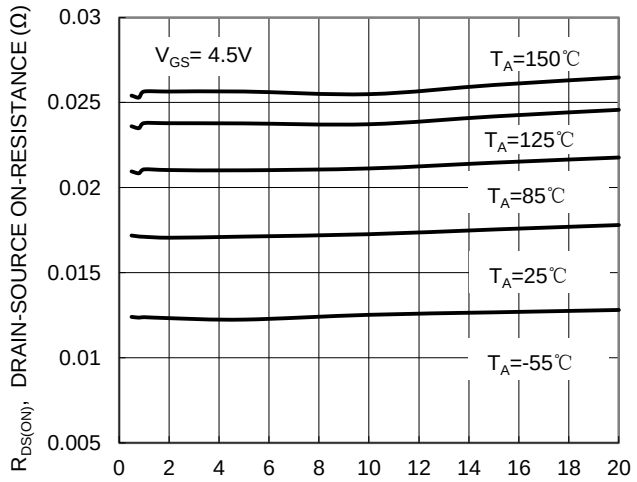

Figure 5. Typical On-Resistance vs. Drain Current and Temperature

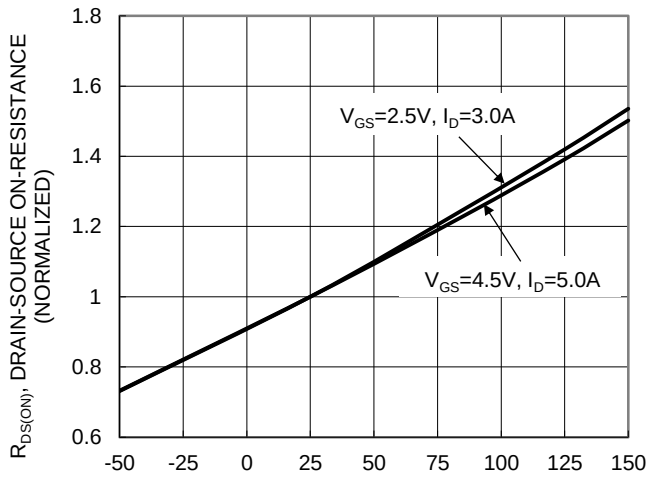

Figure 6. On-Resistance Variation with Temperature

NEW PRODUCT

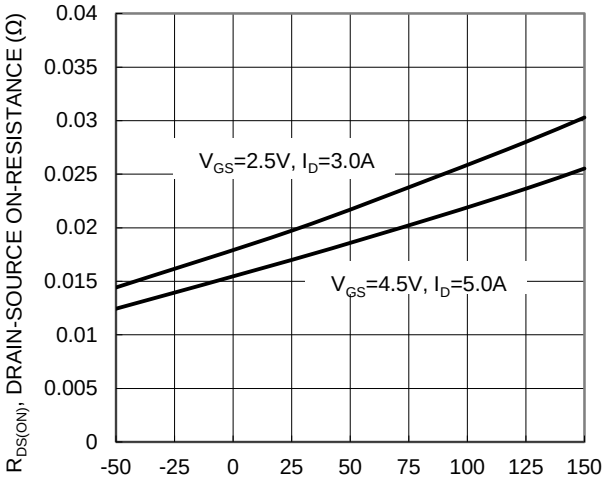

Figure 7. On-Resistance Variation with Temperature

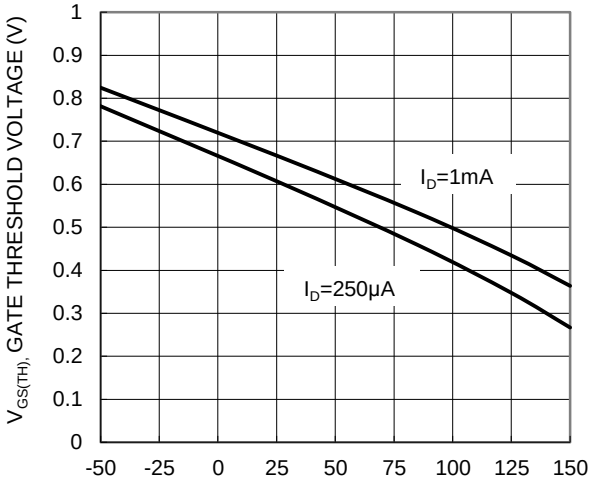

Figure 8. Gate Threshold Variation vs. Junction Temperature

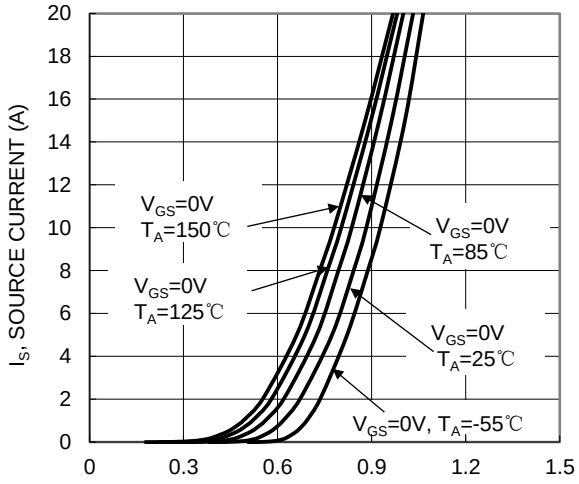

Figure 9. Diode Forward Voltage vs. Current

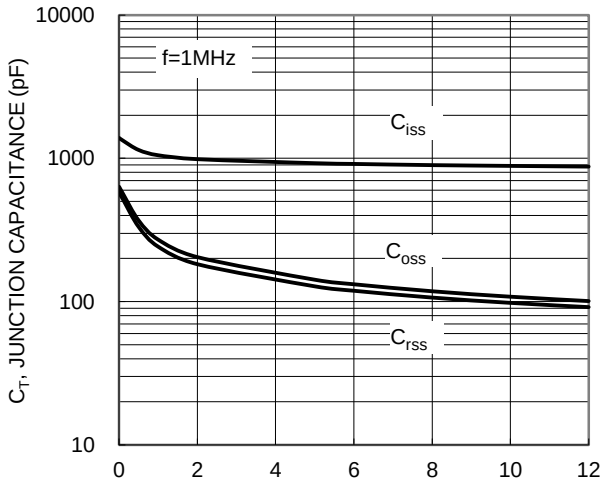

Figure 10. Typical Junction Capacitance

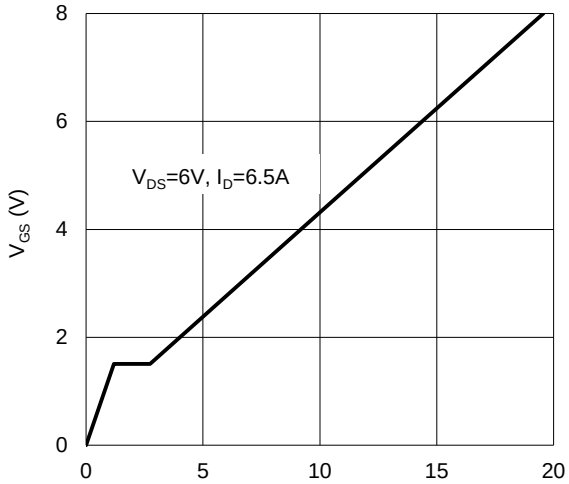

Figure 11. Gate Charge

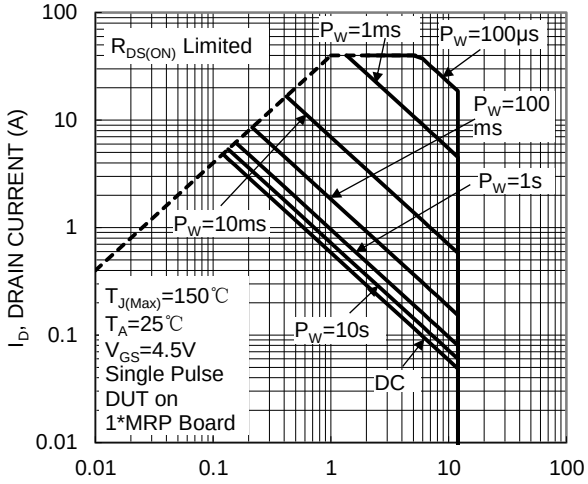

Figure 12. SOA, Safe Operation Area

NEW PRODUCT

Typical Characteristics - P-CHANNEL

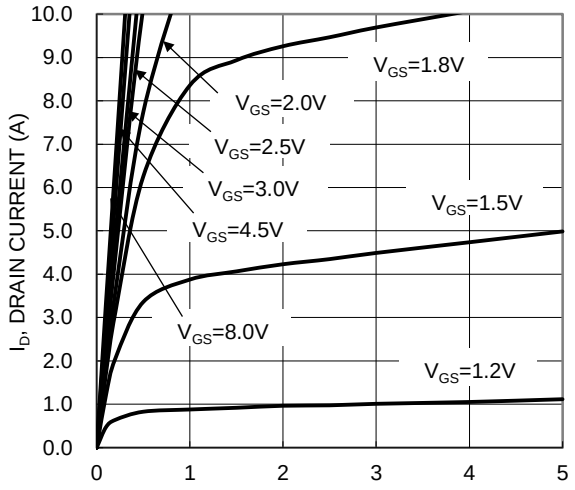

Figure 13. Typical Output Characteristic

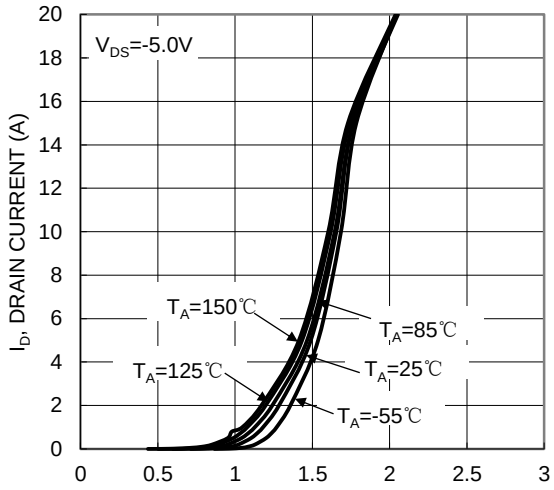

Figure 14. Typical Transfer Characteristic

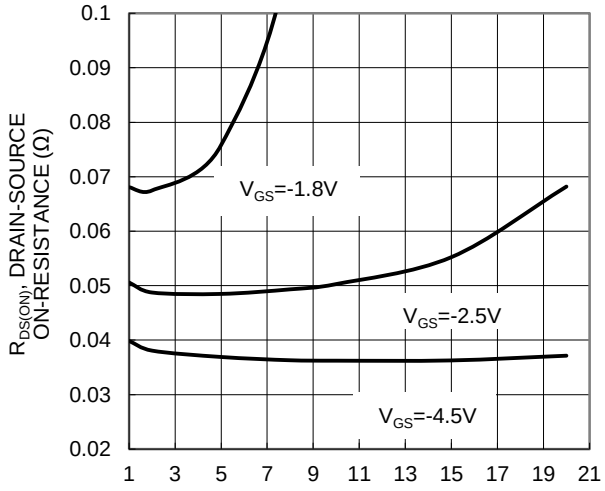

Figure 15. Typical On-Resistance vs Drain Current and Gate Voltage

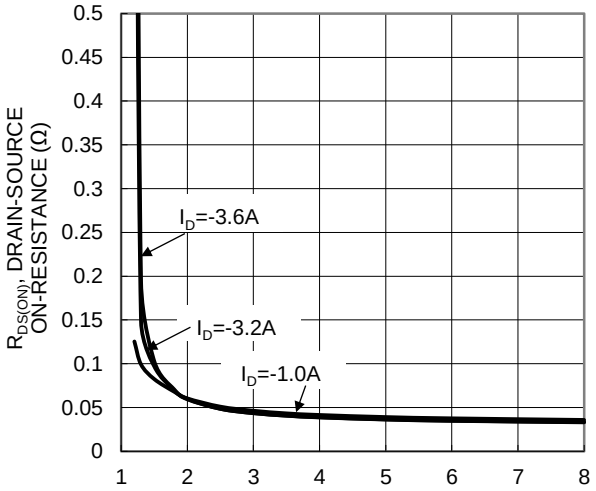

Figure 16. Typical Transfer Characteristic

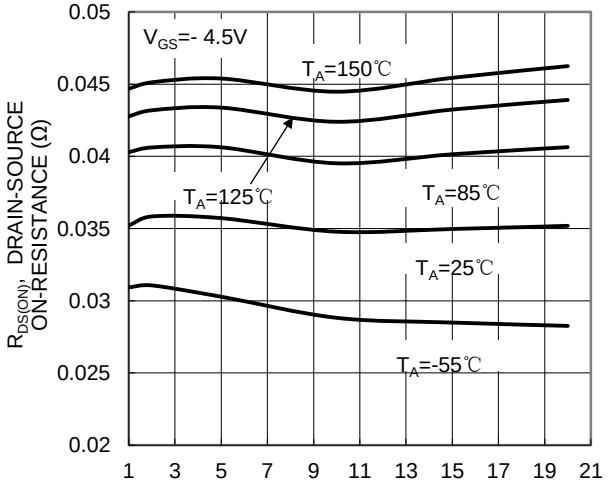

Figure 17. Typical On-Resistance vs Drain Current and Temperature

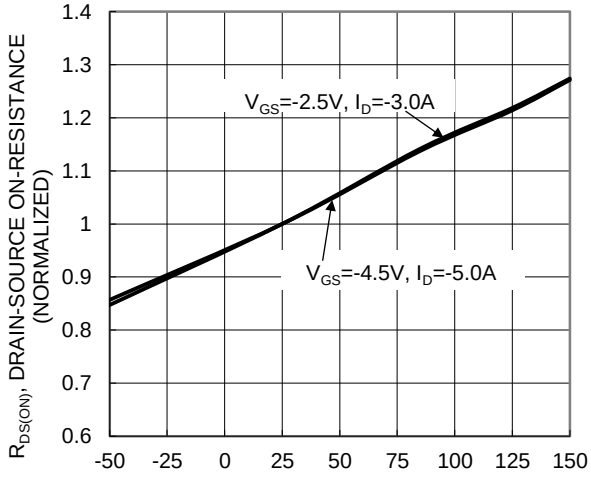

Figure 18. On-Resistance Variation with Temperature

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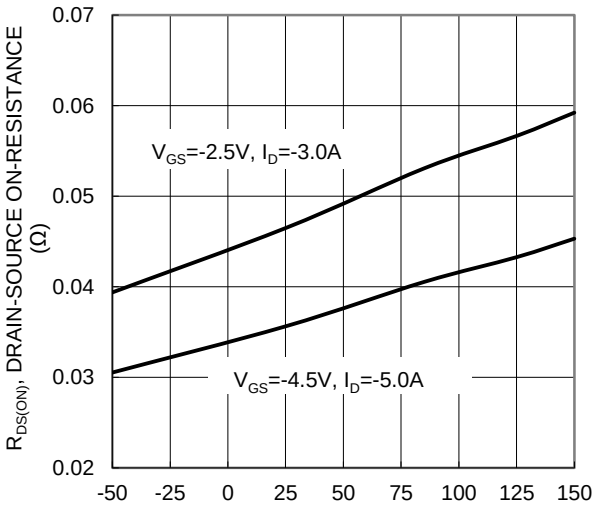

Figure 19. On-Resistance Variation with Temperature

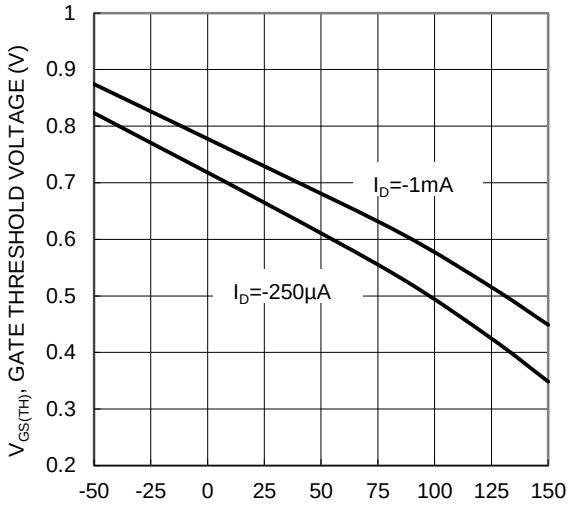

Figure 20. Gate Threshold Variation vs Junction Temperature

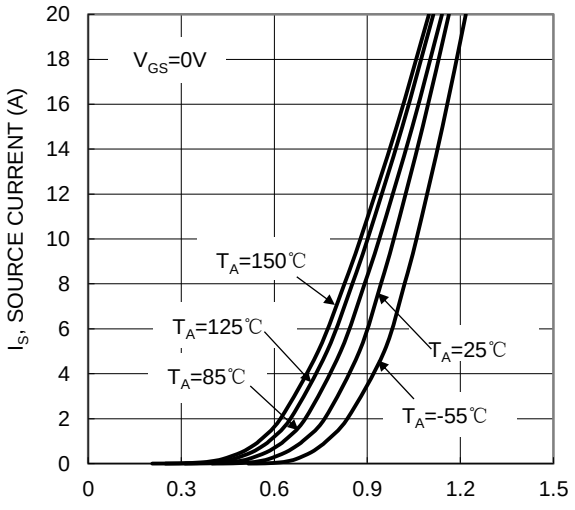

Figure 21. Diode Forward Voltage vs. Current

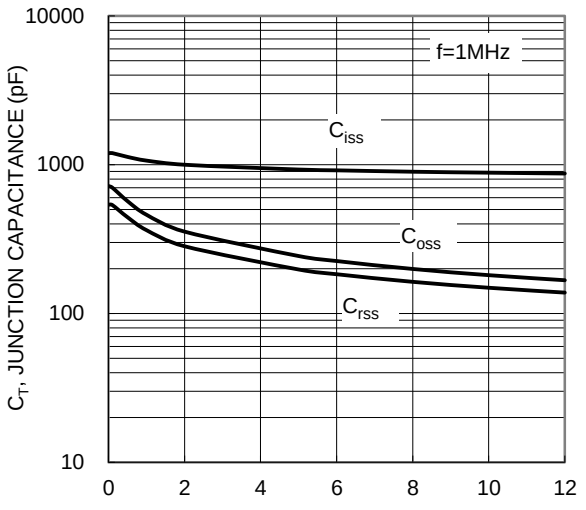

Figure 22. Typical Junction Capacitance

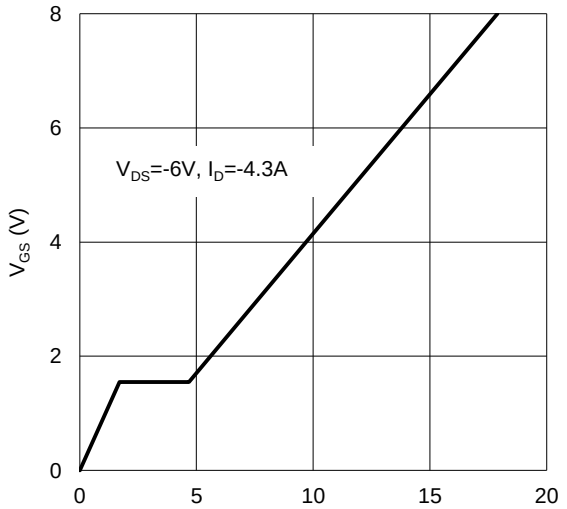

Figure 23. Gate Charge

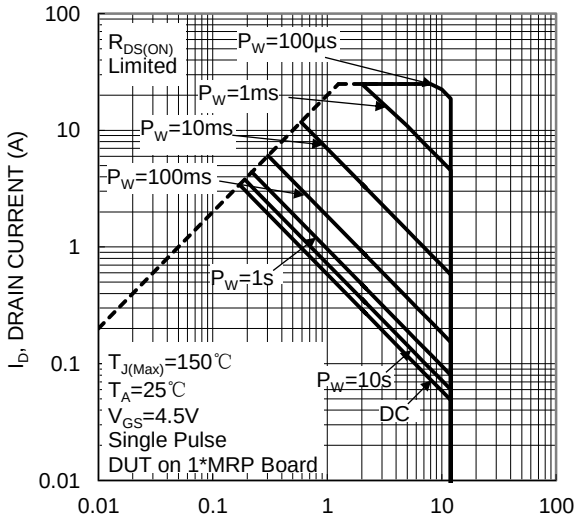

Figure 24. SOA, Safe Operation Area

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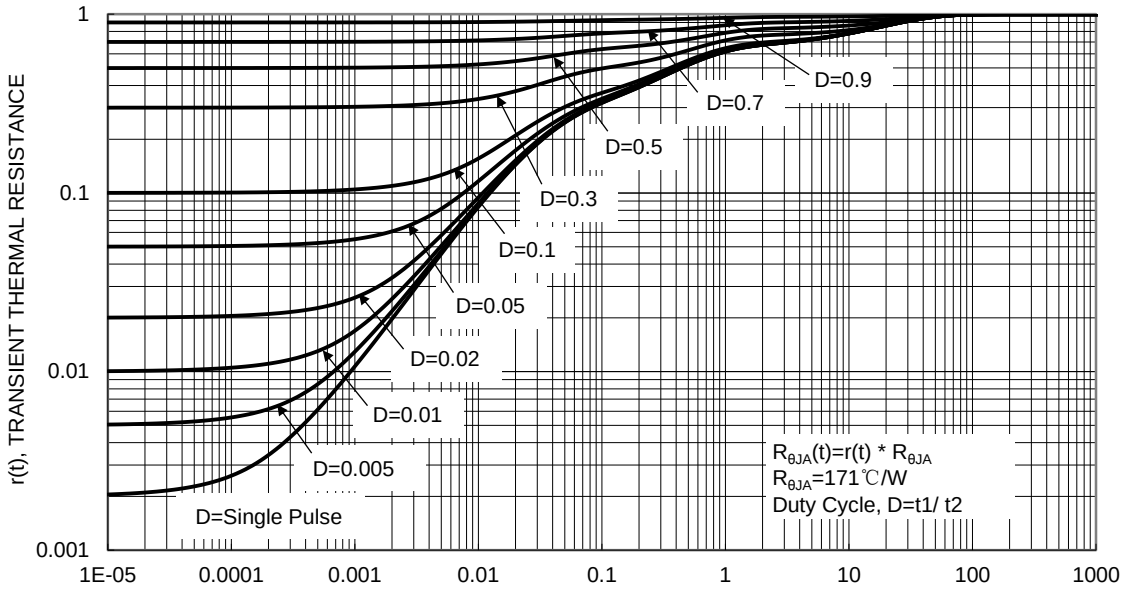
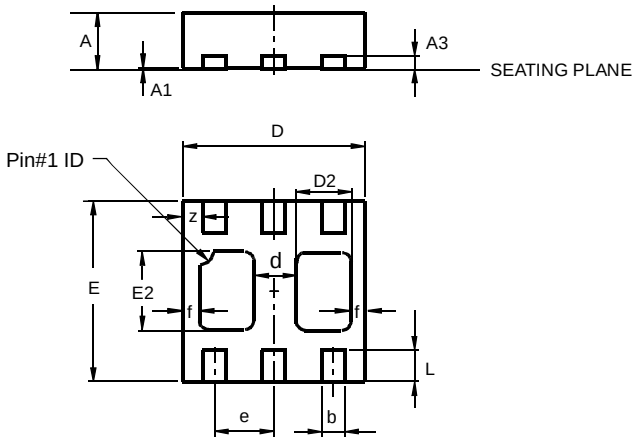


Figure 25. Transient Thermal Resistance

Package Outline Dimensions

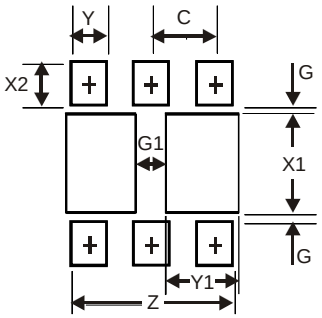
Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN2020-6 Type B			
Dim	**Min**	**Max**	**Typ**
A	0.545	0.605	0.575
A1	0	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
d	—	—	0.45
D2	0.50	0.70	0.60
e	—	—	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
f	—	—	0.15
L	0.25	0.35	0.30
z	—	—	0.225
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Y	0.37
Y1	0.70
C	0.65

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2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

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